

# DPS2015 Timetable

## November 5

8:00		
8:10		
8:20		
8:30	Registration	
8:40		
8:50		
9:00		
9:10	Opening Remark (T. Okumura) Young Award, Nishizawa Award (S. Hamaguchi)	
9:20	<Nisizawa Award> Dr. Kiyoshi Asakawa (Tsukuba Univ.)	
9:30	"Outstanding contribution to the progress of the plasma etching processes for compound materials"	
9:40		
9:50	A-1 <Invited>	Session A Atomic Layer Reactions -1
10:00	Dr. Ying Zhang (Applied Materials)	
10:10	"A New Frontier of Plasma Patterning: Atomic Layer Etch"	
10:20		
10:30	A-2 <Invited>	Session B Surface Reaction
10:40	Dr. Erwin Kessels (Eindhoven Univ. of Technol.)	
10:50	"Plasma-based atomic layer deposition and etching: progress and prospects"	
11:00		
11:10	Break	
11:20		
11:30	B-1 Y. Ohya,	Session C Novel Dry Process and Equipment
11:40	"Clarification of a SiOF layer formed on SiO <sub>2</sub> under fluorocarbon plasma etching"	
11:50	B-2 K. Karahashi,	
12:00	"SiO <sub>2</sub> and Si <sub>3</sub> N <sub>4</sub> etching characteristics of silicon halide ions (SiCl <sub>4</sub> <sup>+</sup> , SiBr <sub>4</sub> <sup>+</sup> )"	
12:10	B-3 N. Nakazaki,	Session D Diagnostics and simulation
12:20	"Experimental demonstration of oblique ion incidence with sheath control plates during plasma etching of silicon"	
12:30	B-4 P. D. Szkutnik, "Plasma Enhanced Metal-Organic Chemical Vapor Deposition of low carbon and conformal Ge,Sb,Te <sub>2</sub> layer for innovative PCRAM applications"	
12:40	Photo Session	
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13:20	Lunch	
13:30		
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14:10	C-1 <Invited>	Session E Dry process for novel materials
14:20	Mr. Hirokazu Ueda (Tokyo Electron)	
14:30	"Conformal doping using a radial line slot antenna microwave plasma source"	
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14:50	C-2 O. Pollet, "Silicon nitride etching by light ion implantation: a comprehensive study of layer modification and selective removal"	
15:00		
15:10	C-3 T. Seki,	
15:20	"Reactive etching with ClF <sub>3</sub> -Ar neutral cluster beam"	
15:30	C-4 S. Okita,	
15:40	"Improvement of the chip flexural strength by the Plasma Dicing technology"	
15:50	Break	
16:00		
16:10	D-1 A. Pandey,	
16:20	"Effect of surface magnetic confinement on production of large-volume pulsed plasma"	
16:30	D-2 S. Numazawa,	
16:40	"Molecular dynamics study on fluorine radical multilayer adsorption during Si, SiO <sub>2</sub> or Si <sub>3</sub> N <sub>4</sub> etching processes"	
16:50	E-1 H. Zhang, "High Density Formation of Fe-silicide Nanodots Induced by Remote H2 Plasma and Characterization of Their Crystalline Structure and Magnetic Properties"	
17:00	E-2 J. Shin,	
17:10	"Fabrication of sub-50nm Al <sub>2</sub> O <sub>3</sub> nanotube structure by Block copolymer (BCP)"	
17:20	E-3 N. Gosset,	
17:30	"Surface state improvement in GaN deep etching for power electronics applications"	
17:40	E-4 T. Nakatani, "Fabrication of Thin Film Transistors by Atmospheric Pressure Micro-Thermal-Plasma-Jet Irradiation on Amorphous Germanium Strips"	
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19:30	Banquet	
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## November 6

8:00		
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8:30	Registration	
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9:10	F-1 <Invited>	Session F High Aspect Ratio Etching
9:20	Dr. Sebastian Engelmann (IBM), "Improving high aspect ratio processes for logic applications through gas chemistry and plasma discharge optimization"	
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9:50	F-2 T. Iwase,	Session G Atomic Layer Reactions -2
10:00	"Role of surface-reaction-layer formed by high-aspect-ratio etching of poly-Si/SiO <sub>2</sub> stacks"	
10:10	F-3 P. Barros,	
10:20	"DSA planarization approach to solve pattern density issue"	
10:30	F-4 F. Leroy,	Session H Plasma Induced Damage
10:40	"Cryoetching processes applied to ULK material"	
10:50	Break	
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11:40	Poster	
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13:10	Lunch	
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14:00	G-1 <Invited>	Session H Plasma Induced Damage
14:10	Dr. Peter Ventzek (Tokyo Electron America)	
14:20	"Control of Atomic Layer Reactions for Plasma Processing"	
14:30		
14:40	G-2 <Invited>	
14:50	Dr. Chris Lee (Lam Research)	
15:00	"Variability Control Using Atomic Layer Processing"	
15:10	G-3 G. Yuan, "Role of physisorption and chemisorption during hot-wire-assisted atomic layer deposition of nickel film examined by step coverage analysis"	
15:20		
15:30	Break	
15:40		
15:50	H-1 Y. Miyoshi,	
16:00	"Effect of transient behavior of pulse modulated inductively coupled plasma on photon-induced interface defects"	
16:10	H-2 Y. Okada,	
16:20	"Surface orientation dependence of plasma-induced ion bombardment damage in Si substrate"	
16:30	H-3 K. Nishida,	
16:40	"A new electrical evaluation method to characterize low-k dielectric damage during plasma processing"	
16:50	Closing Remark (M. Honda)	
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